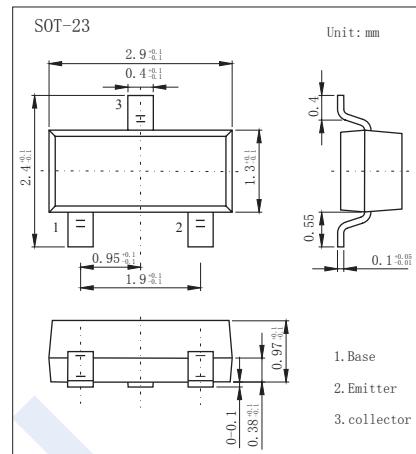


**NPN Transistors****2SC2295****■ Features**

- High transition frequency  $f_T$ .
- Complementary to 2SA1022

**■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$** 

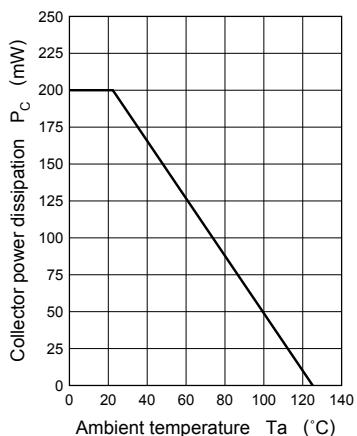
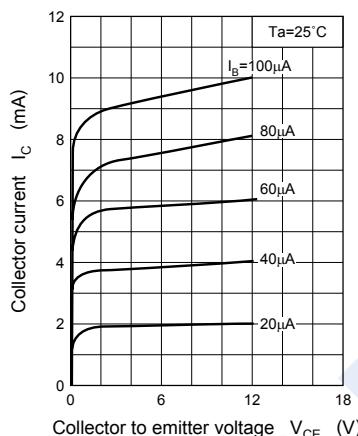
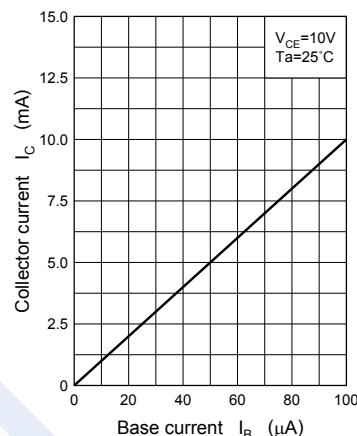
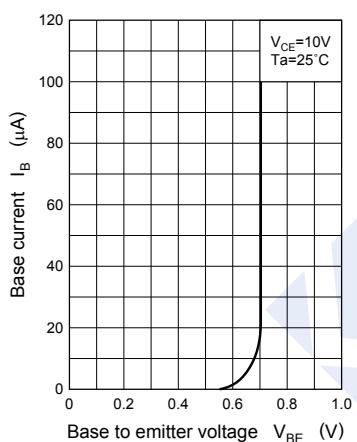
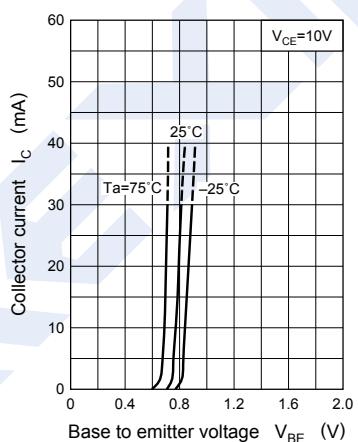
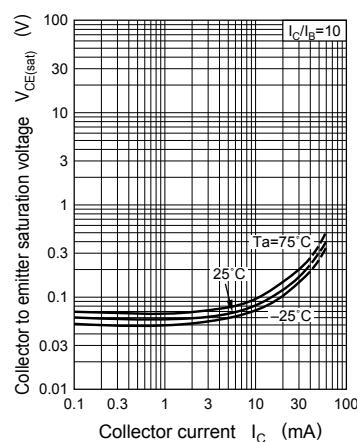
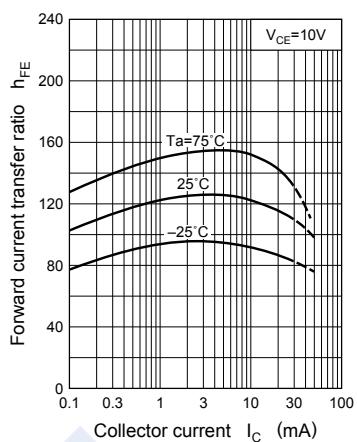
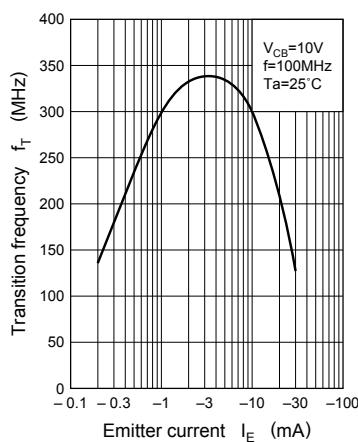
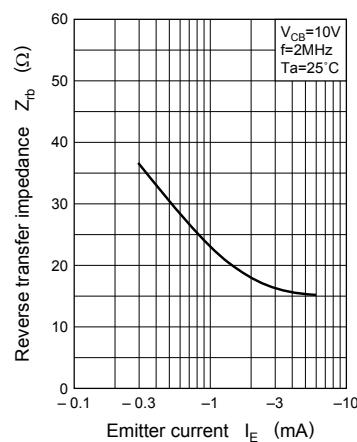
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	30	V
Collector - Emitter Voltage	$V_{CEO}$	20	
Emitter - Base Voltage	$V_{EBO}$	5	
Collector Current - Continuous	$I_C$	30	
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	30			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	20			
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 30 \text{ V}, I_E = 0$			100	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			100	nA
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -10 \text{ mA}, I_B = 1\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = -10 \text{ mA}, I_B = 1\text{mA}$			1.2	
DC current gain	$\text{h}_{FE}$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	70		220	
Noise figure	NF	$V_{CB} = 10\text{V}, I_E = -1\text{mA}, f = 5\text{MHz}$		2.8	4	dB
Reverse transfer impedance	$Z_{rd}$	$V_{CB} = 10\text{V}, I_E = -1\text{mA}, f = 2\text{MHz}$		22	50	$\Omega$
Common emitter reverse transfer capacitance	$C_{re}$	$V_{CE} = 10\text{V}, I_C = 1\text{mA}, f = 10.7\text{MHz}$			1.5	pF
Transition frequency	$f_T$	$V_{CB} = 10\text{V}, I_E = -1\text{mA}, f = 200\text{MHz}$	150	250		MHz

**■ Classification of  $\text{h}_{fe}$** 

Type	2SC2295-B	2SC2295-C
Range	70-140	110-220
Marking	VB	VC

**NPN Transistors****2SC2295****■ Typical Characteristics** $P_C - Ta$  $I_C - V_{CE}$  $I_C - I_B$  $I_B - V_{BE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $Z_{rb} - I_E$ 

## NPN Transistors

### 2SC2295

#### ■ Typical Characteristics

